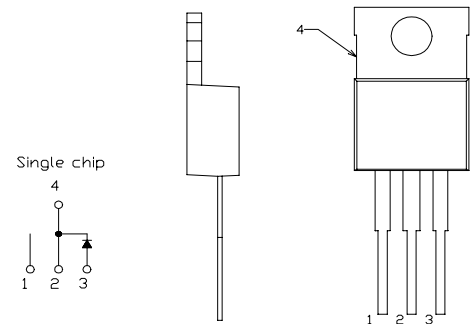


FRD Type : GSF10A60B

OUTLINE DRAWING

FEATURES

- * Similar to TO-220AB Case
- * Ultra – Fast Recovery
- * Low Forward Voltage Drop
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * 200 Volts thru 600 Volts Types Available



Maximum Ratings

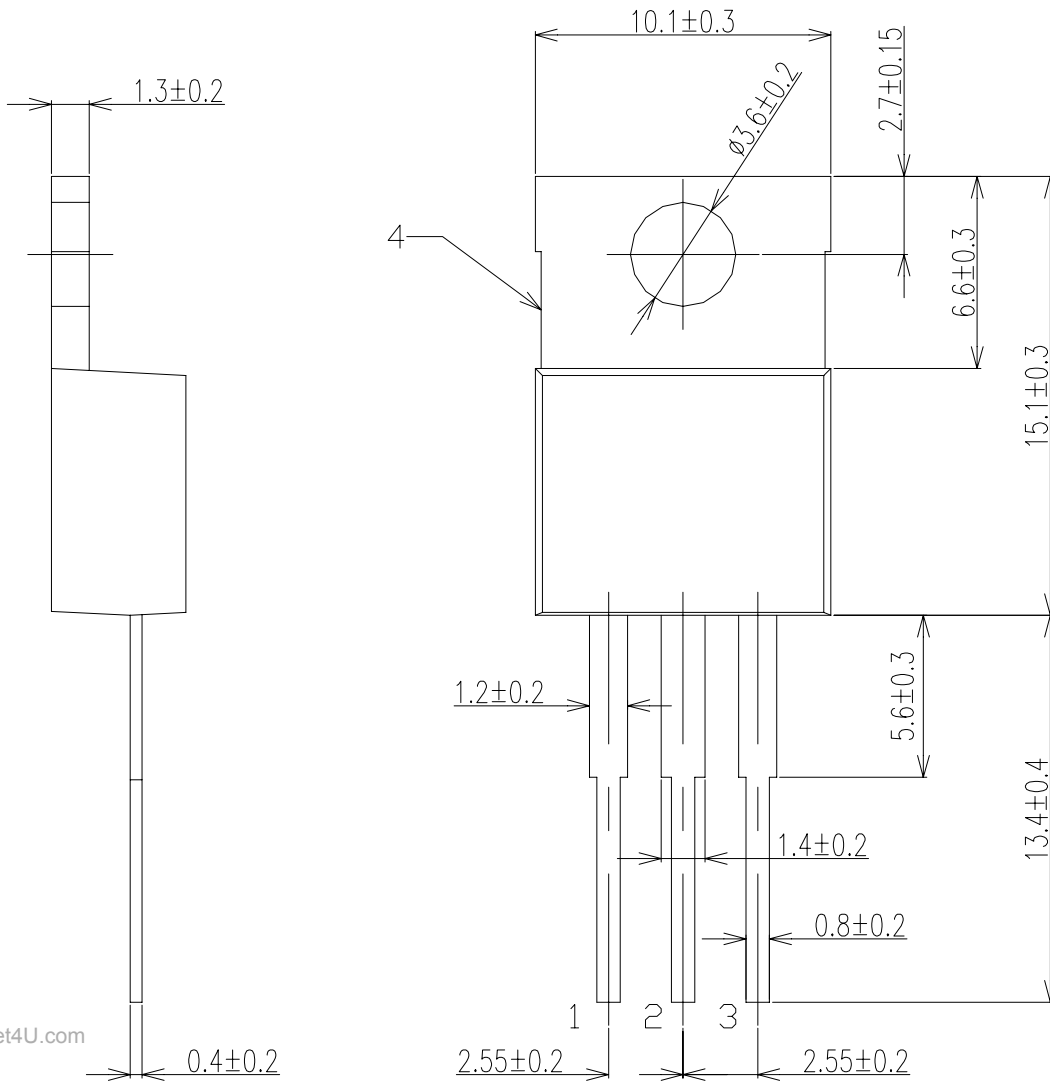
Approx Net Weight:1.9g

Rating	Symbol	GSF10A60B		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	600		V
Average Rectified Output Current	I_O	10	$T_c=74^{\circ}C$ 50 Hz Half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	I_{FSM}	120	50 Hz Half Sine Wave, 1 cycle Non-repetitive	A
Operating Junction Temperature Range	T_{jw}	- 40 to + 150		$^{\circ}C$
Storage Temperature Range	T_{stg}	- 40 to + 150		$^{\circ}C$
Mounting torque		0.5	Recommended value	N.m

Electrical • Thermal Characteristics

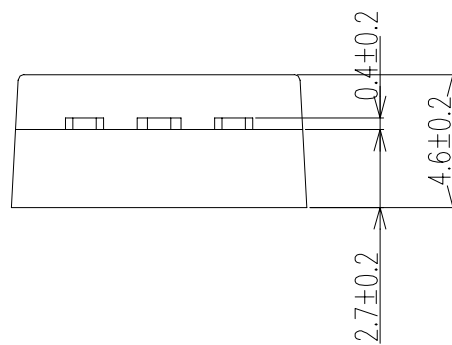
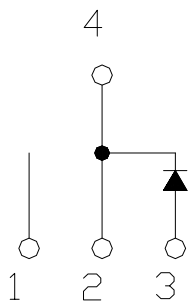
Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$	-	-	30	μA
Peak Forward Voltage	V_{FM}	$T_j= 25^{\circ}C, I_{FM}= 10A$	-	-	1.8	V
Reverse Recovery Time	trr	$I_{FM}= 10A,$ $-di/dt= 50 A/\mu s, T_a= 25^{\circ}C$	-	-	50	ns
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	4	$^{\circ}C/W$

GSF_B_ OUTLINE DRAWING (Dimensions in mm)

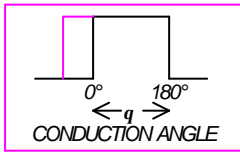
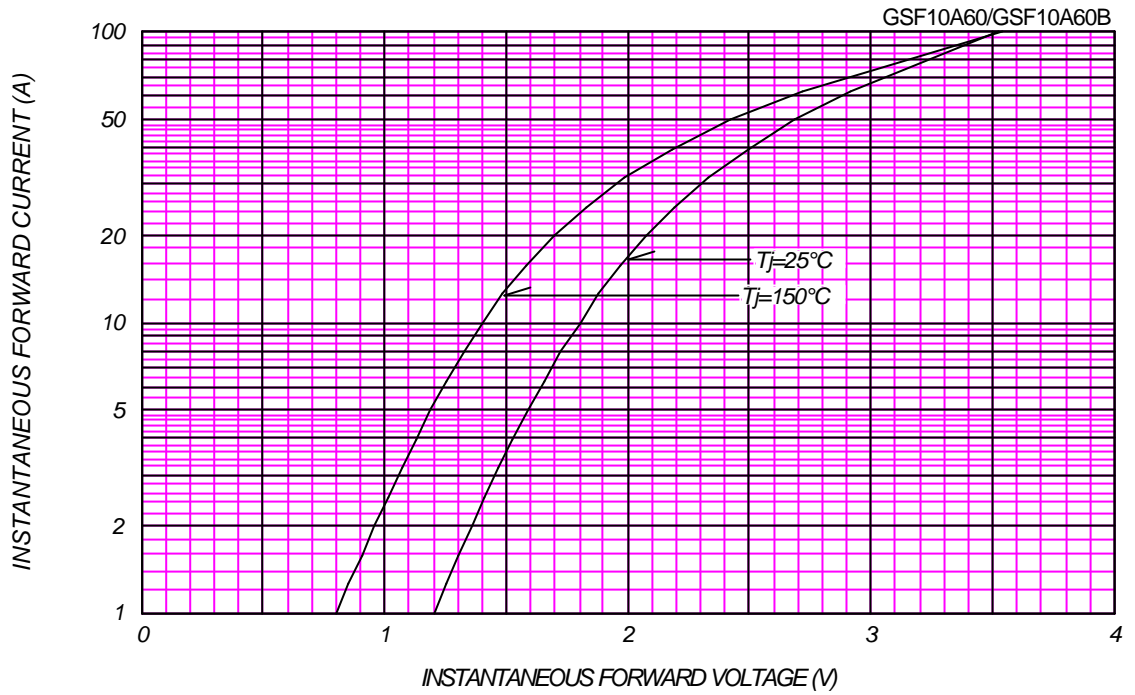


www.DataSheet4U.com

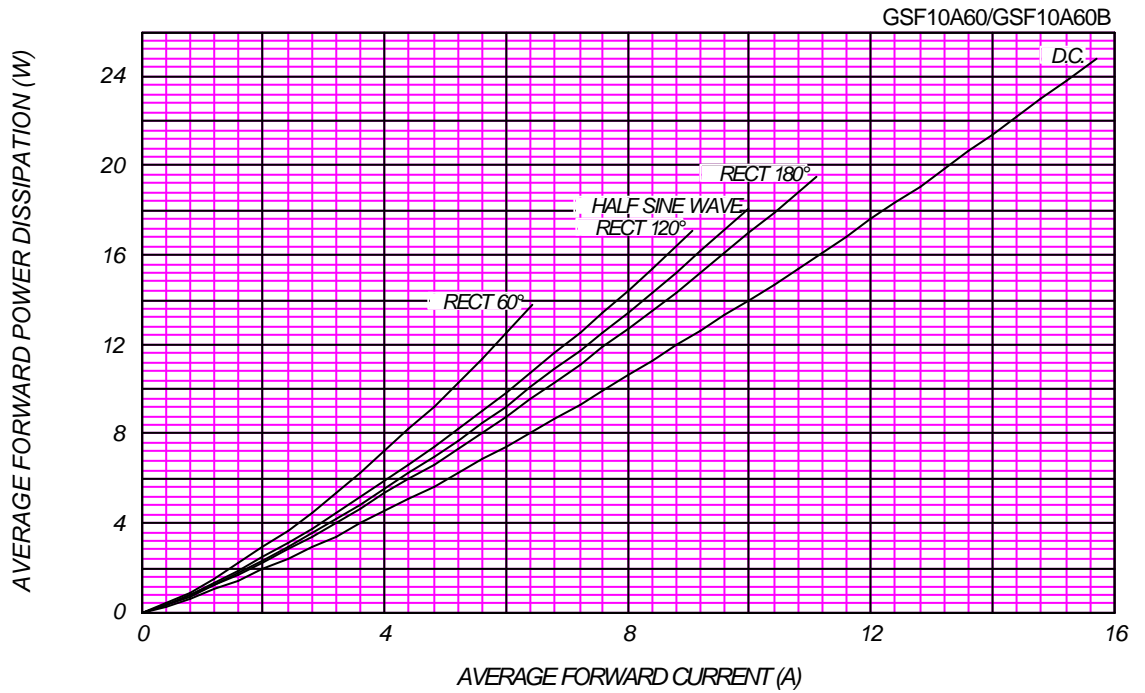
Single chip

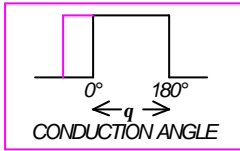


FORWARD CURRENT VS. VOLTAGE

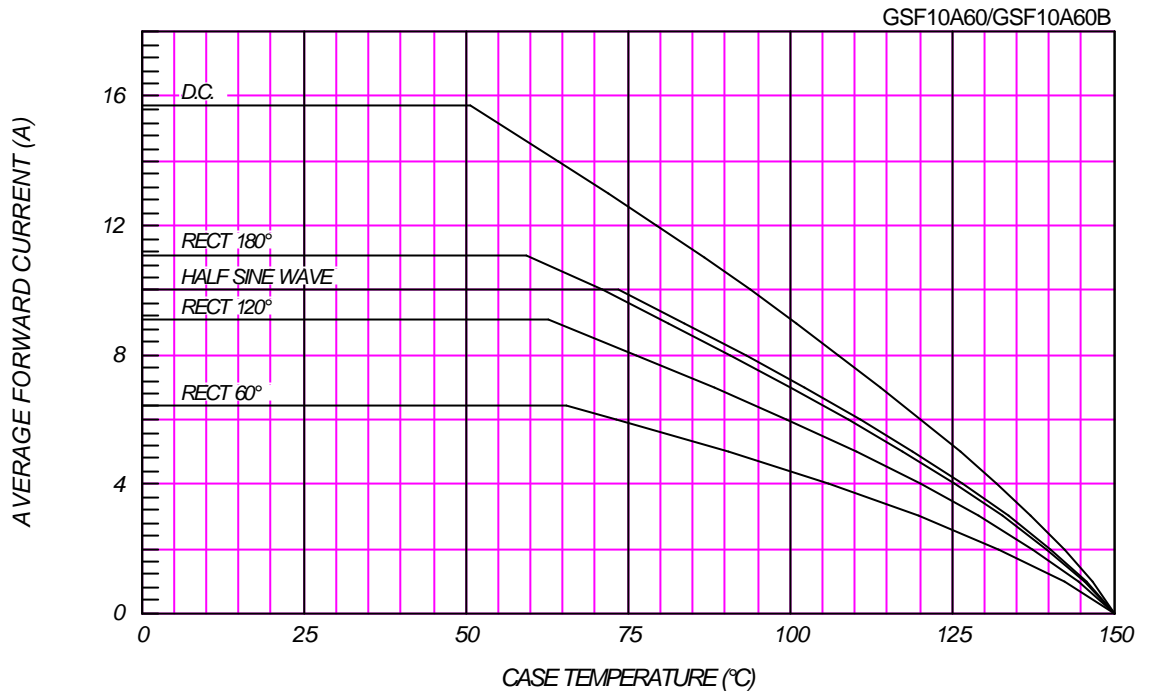


AVERAGE FORWARD POWER DISSIPATION





AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE



SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

